DISCRETE SEMICONDUCTORS

DATA SHEET

BTA212B series B Three quadrant triacs high commutation

Product specification

September 1997



Three quadrant triacs high commutation

BTA212B series B

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope suitable for surface mounting intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

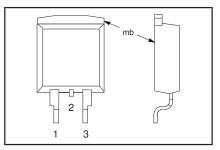
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} $I_{T(RMS)}$ I_{TSM}	BTA212B- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500B 500 12 95	600B 600 12 95	800B 800 12 95	V A A

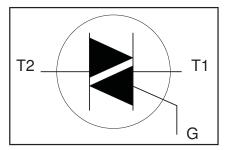
PINNING - SOT404

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
mb	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V_{DRM}	Repetitive peak off-state voltages		-	-500 500¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-		12		A
I _{TSM}	Non-repetitive peak on-state current	$T_{mb} \le 99 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge t = 20 ms t = 16.7 ms	-		95 105		A A
l ² t dl _T /dt	I ² t for fusing Repetitive rate of rise of on-state current after triggering	t = 10.7 ms t = 10 ms l _{TM} = 20 A; l _G = 0.2 A; dl _G /dt = 0.2 A/µs	-		45 100		A A ² s A/μs
I _{GM} V _{GM} P _{GM} P _{G(AV)}	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms	- - -		2 5 5 0.5		A V W W
T _{stg}	Storage temperature Operating junction temperature	portou	-40 -		150 125		Ç

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μ s.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th i-a}	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air		- - 60	1.5 2.0 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		T2+ G+	2	18	50	mA
		T2+ G-	2	21	50	mA
		T2- G-	2	34	50	mA
l IL	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
		T2+ G+	-	31	60	mA
		T2+ G-	-	34	90	mA
		T2- G-	-	30	60	mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	31	60	mA
$V_{T}^{I_{H}}$	On-state voltage	$I_T = 17 \text{ A}$	-	1.3	1.6	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 \text{ °C}$	0.25	0.4	-	V
I_{D}	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	4000	-	V/μs
	off-state voltage Critical rate of change of commutating current	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 12 \text{ A};$ without snubber; gate open circuit	-	24	-	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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² Device does not trigger in the T2-, G+ quadrant.

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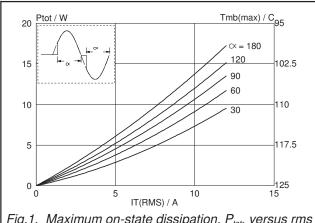


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

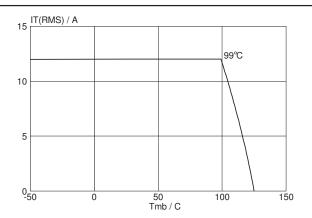


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

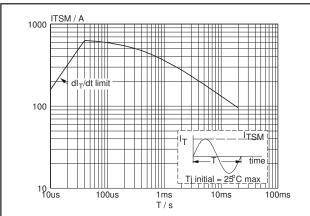


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

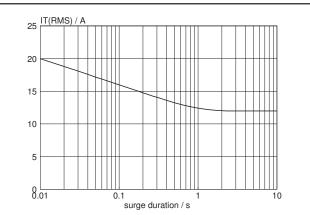


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50~Hz; $T_{mb} \le 99 ^{\circ}C$.

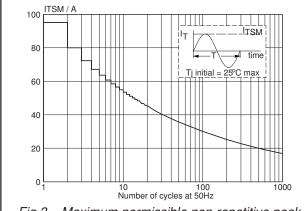


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

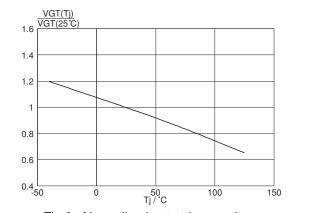
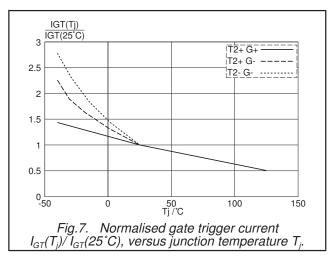
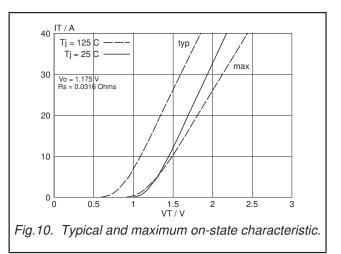


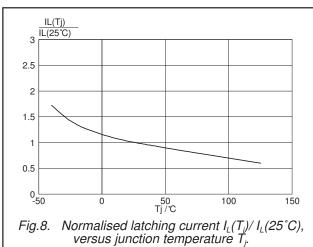
Fig.6. Normalised gate trigger voltage $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$, versus junction temperature T_i .

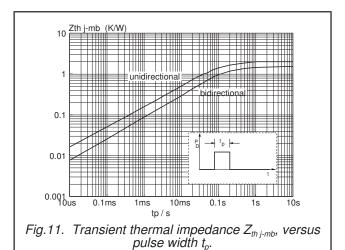
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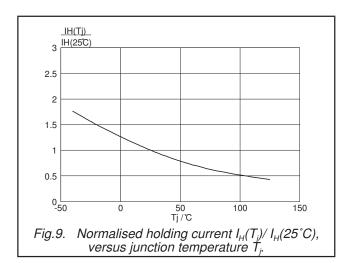
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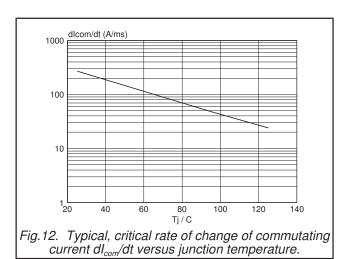








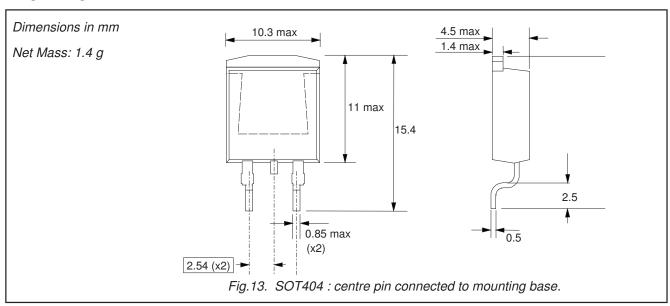




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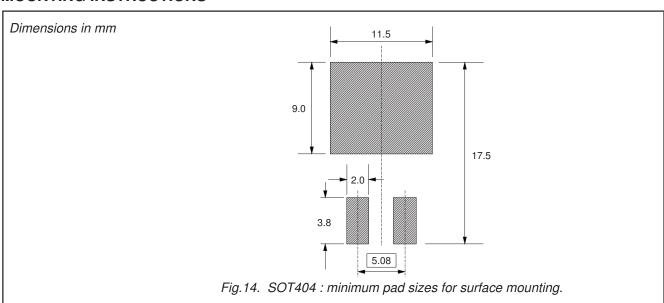
MECHANICAL DATA



Notes

1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet Production This document contains the product specification.		This document contains the product specification.

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